

	Hits	Search Text	DBs
34	8	((resist or photoresist) near16 pattern\$4 near29 mask) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4) near12 strip\$4 near16 ((resist or photoresist) near6 (pattern\$3 or mask)) near12 (residu\$4 or remain\$4)) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (substrate or device or wafer) same (resist or photoresist) same pattern)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
35	124	((resist or photoresist) near16 pattern\$4 near29 mask) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4 or post\$4expos\$5 or post\$8develop\$5) near12 (remov\$4 or strip\$4) near16 ((resist or photoresist) near6 (pattern\$3 or mask)) near16 (residu\$4 or remain\$4 or remnant)) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (substrate or device or wafer) same (resist or photoresist) same pattern\$3 same (etch\$4 or RIE))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
36	18	((resist or photoresist) near16 pattern\$4 near29 mask) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4 or post\$4expos\$5 or post\$8develop\$5) near12 (strip\$4) near16 ((resist or photoresist) near6 (pattern\$3 or mask)) near16 (residu\$4 or remain\$4 or remnant)) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (substrate or device or wafer) same (resist or photoresist) same pattern\$3 same (etch\$4 or RIE))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
37	1	((resist or photoresist) near16 pattern\$4) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4 or post\$4expos\$5 or post\$8develop\$5) near16 ((resist or photoresist) near26 (pattern\$3 or mask)) near16 (residu\$4 or remain\$4 or remnant)) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (substrate or device or wafer) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone)) and strip\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
38	3	((resist or photoresist) near16 pattern\$4) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4 or post\$4expos\$5 or post\$8develop\$5) near16 ((resist or photoresist) near26 (pattern\$3 or mask))) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (substrate or device or wafer) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone)) and strip\$4 and residu\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
39	45	S45 NOT S44	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
40	12	((resist or photoresist) near16 pattern\$4) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminat\$4 or post\$4expos\$5 or post\$8develop\$5) near16 ((resist or photoresist) near26 (pattern\$3 or mask))) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone)) and strip\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
41	42	((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist)) and ((expos\$4 or illuminat\$4 or irradiat\$4) near5 (time or seconds or minute))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
42	23	((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate)) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist) same ((expos\$4 or illuminat\$4 or irradiat\$4) near5 (time or "seconds" or minute)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
43	13	((resist or photoresist) near16 pattern\$4) and ((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist)) and strip\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
44	58	((resist or photoresist) near16 pattern\$4) and (((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
45	27	((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist) same (expos\$4 or illuminat\$4 or irradiat\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
46	6	((Aluminum or TFT or transistor or Ti or titanium or Mb or molybdenum or Ta or tantulum or tungsten or metal\$4 or conductive or gate) near26 electrode) same (resist or photoresist) same (pattern\$3 or mask) same (etch\$4 or RIE)) and ((photosensitizer or DNQ or diazonaphthoquinone) same (photoresist or resist) same (expos\$4 or illuminat\$4 or irradiat\$4) same (PEB or post\$4imag\$4 or post\$4expos\$6))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB